

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings of claims in the application:

**Listing of Claims:**

1. (Original) A method of depositing a silica glass insulating film over a substrate, the method comprising:
  - exposing the substrate to a silicon-containing reactant introduced into a chamber in which the substrate is disposed such that one or more layers of the silicon-containing reactant are adsorbed onto the substrate;
  - purging or evacuating the chamber of the silicon-containing reactant;
  - converting the silicon-containing reactant into a silica glass insulating compound by exposing the substrate to oxygen radicals formed from a second reactant while biasing the substrate to promote a sputtering effect; and
  - repeating the exposing, purging/evacuating and exposing sequence a plurality of times.
2. (Original) The method of claim 1 wherein an average atomic mass of all atomic constituents in the second reactant is less than or equal to an average atomic mass of oxygen.
3. (Original) The method of claim 1 wherein the silicon-containing reactant is a silane family member having a formula of  $\text{Si}_n\text{H}_{2n+2}$ .
4. (Original) The method of claim 3 wherein the second reactant consists of molecular oxygen ( $\text{O}_2$ ).
5. (Original) The method of claim 1 wherein the second reactant consists of molecular oxygen ( $\text{O}_2$ ) and a sputtering agent.
6. (Original) The method of claim 5 wherein the sputtering agent consists of molecular hydrogen ( $\text{H}_2$ ).
7. (Currently Amended) The method of claim 5 wherein the ~~light-weight~~ sputtering agent comprises molecular hydrogen ( $\text{H}_2$ ) and/or helium.

8. (Original) The method of claim 1 wherein the oxygen radicals are generated by forming a plasma within the chamber.
9. (Original) The method of claim 1 wherein the oxygen radicals are generated by forming a plasma in a remote plasma chamber.
10. (Original) The method of claim 1 wherein the chamber is evacuated of the silicon-containing reactant prior to exposing the substrate to oxygen radicals.
11. (Original) The method of claim 1 wherein the chamber is purged of the silicon-containing reactant by flowing a gas that is chemically inert to silica glass into the chamber.
12. (Original) The method of claim 1 wherein the chamber is purged of the silicon-containing reactant by flowing an oxygen source into the chamber.
13. (Original) The method of claim 8 wherein energy is applied to the chamber to form a plasma from the second reactant while biasing the substrate and wherein no plasma is formed while the substrate is exposed to the silicon-containing reactant.
14. (Original) The method of claim 1 further comprising doping the silica glass film with a dopant.
15. (Original) A method of depositing a silica glass insulating film over a substrate having a gap formed between two adjacent raised features, the gap having a bottom surface and a sidewall surface, the method comprising:
  - exposing the substrate to a silicon-containing reactant introduced into a chamber in which the substrate is disposed such that one or more layers of the silicon containing reactant are adsorbed onto the substrate;
  - purging or evacuating the chamber of the silicon-containing reactant;
  - converting the silicon-containing reactant into a silica glass insulating compound by exposing the substrate to a plasma formed from a second reactant comprising oxygen atoms while biasing the substrate to promote a sputtering effect, wherein an average atomic mass of all atomic constituents in the second reactant is less than or equal to an average atomic mass of oxygen; and

repeating the exposing, purging/evacuating and exposing sequence a plurality of times;

wherein the substrate is maintained at a temperature between 300-800°C during growth of the silica glass film and wherein the silica glass film grows up from the bottom surface of the gap at a rate greater than it grows inward on the sidewall surface of the gap.